

74AUP2G00GF,115 Datasheet



DiGi Electronics Part Number Manufacturer Manufacturer Product Number Description Detailed Description

er 74AUP2G00GF,115-DG er Nexperia USA Inc. er 74AUP2G00GF,115 in IC GATE NAND 2CH 2-INP 8XSON NAND Gate IC 2 Channel 8-XSON (1.35x1)

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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:					
74AUP2G00GF,115	Nexperia USA Inc.					
Series:	Product Status:					
74AUP	Obsolete					
Logic Type:	Number of Circuits:					
NAND Gate	2					
Number of Inputs:	Features:					
2						
Voltage - Supply:	Current - Quiescent (Max):					
0.8V ~ 3.6V	500 nA					
Current - Output High, Low:	Input Logic Level - Low:					
4mA, 4mA	0.7V ~ 0.9V					
Input Logic Level - High:	Max Propagation Delay @ V, Max CL:					
1.6V ~ 2V	6.5ns @ 3.3V, 30pF					
Operating Temperature:	Mounting Type:					
-40°C ~ 125°C	Surface Mount					
Supplier Device Package:	Package / Case:					
8-XSON (1.35x1)	8-XFDFN					
Base Product Number:						
74AUP2G00						

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8542.39.0001	



1. General description

The 74AUP2G00 provides dual 2-input NAND function.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - JESD8-12 (0.8 V to 1.3 V)
 - JESD8-11 (0.9 V to 1.65 V)
 - JESD8-7 (1.2 V to 1.95 V)
 - JESD8-5 (1.8 V to 2.7 V)
 - JESD8-B (2.7 V to 3.6 V)
- Low static power consumption; I_{CC} = 0.9 µA (maximum)
- Latch-up performance exceeds 100 mA per JESD78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial power-down mode operation
- ESD protection:
 - HBM: ANSI/ESDA/JEDEC JS-001 class 3A exceeds 5000 V
 - CDM: ANSI/ESDA/JEDEC JS-002 class C3 exceeds 1000 V
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

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3. Ordering information

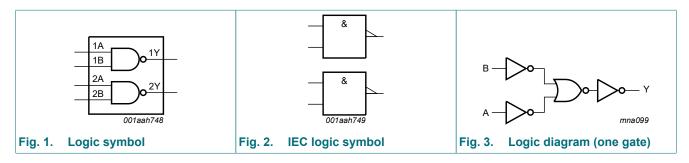
Type number	Package							
	Temperature range Name Description N							
74AUP2G00DC	-40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	<u>SOT765-1</u>				
74AUP2G00GT	-40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 × 1.95 × 0.5 mm	<u>SOT833-1</u>				
74AUP2G00GN	-40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.2 × 1.0 × 0.35 mm	<u>SOT1116</u>				
74AUP2G00GS	-40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 × 1.0 × 0.35 mm	<u>SOT1203</u>				
74AUP2G00GX	-40 °C to +125 °C	X2SON8	plastic thermal enhanced extremely thin small outline package; no leads; 8 terminals; body 1.35 × 0.8 × 0.32 mm	SOT1233-2				

4. Marking

Table 2. Marking codes					
Type number	Marking code[1]				
74AUP2G00DC	p00				
74AUP2G00GT	p00				
74AUP2G00GN	pA				
74AUP2G00GS	pA				
74AUP2G00GX	pA				

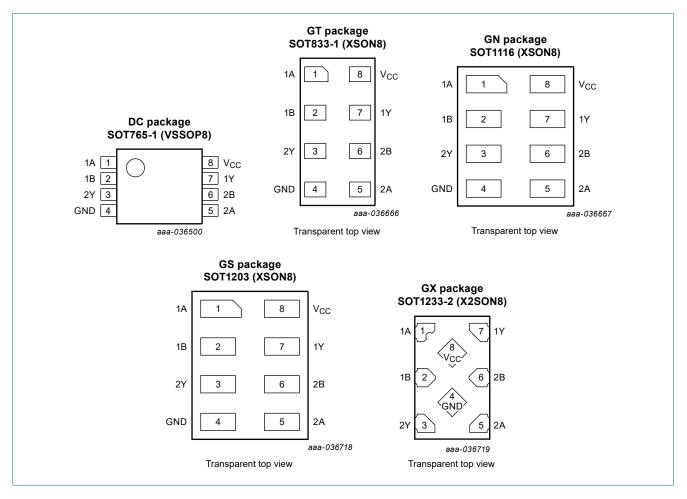
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



6. Pinning information





6.2. Pin description

Table 3. Pin description Pin Symbol Description 1A, 2A 1, 5 data input 1B, 2B 2, 6 data input GND 4 ground (0 V) 1Y, 2Y 7, 3 data output 8 V_{CC} supply voltage

7. Functional description

Table 4. Function table

H = HIGH voltage level; L = LOW voltage level.

Input	Output	
nA	nB	nY
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Мах	Unit
V _{CC}	supply voltage			-0.5	+4.6	V
VI	input voltage		[1]	-0.5	+4.6	V
Vo	output voltage	Active mode and Power-down mode	[1]	-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V		-50	-	mA
I _{OK}	output clamping current	V _O < 0 V		-50	-	mA
lo	output current	$V_{O} = 0 V \text{ to } V_{CC}$		-	±20	mA
I _{CC}	supply current			-	+50	mA
I _{GND}	ground current			-50	-	mA
T _{stg}	storage temperature			-65	+150	°C
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C				
		SOT765-1 (VSSOP8) SOT833-1 (XSON8) SOT1116 (XSON8) SOT1203 (XSON8)	[2]	-	250	mW
		SOT1233-2 (X2SON8)	[3]	-	300	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SOT765-1 (VSSOP8) package: P_{tot} derates linearly with 4.9 mW/K above 99 °C.
 For SOT833-1 (XSON8) package: P_{tot} derates linearly with 3.1 mW/K above 68 °C.
 For SOT1116 (XSON8) package: P_{tot} derates linearly with 4.2 mW/K above 90 °C.
 For SOT1203 (XSON8) package: P_{tot} derates linearly with 3.6 mW/K above 81 °C.

[3] For SOT1233-2 (X2SON8) package: Ptot derates linearly with 7.7 mW/K above 118 °C.

9. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Мах	Unit
V _{CC}	supply voltage		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	0	V _{CC}	V
		Power-down mode; V _{CC} = 0 V	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 0.8 V to 3.6 V	-	200	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
T _{amb} = 2	5 °C				1	
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	$0.70 \times V_{CC}$	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.65 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.30 × V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.35 × V _{CC}	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = -20 µA; V_{CC} = 0.8 V to 3.6 V	V _{CC} - 0.1	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.75 × V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	1.11	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.32	-	-	V
		I _O = -2.3 mA; V _{CC} = 2.3 V	2.05	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.9	-	-	V
		I _O = -2.7 mA; V _{CC} = 3.0 V	2.72	-	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.6	-	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = 20 µA; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.31	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.31	V
		I_0 = 2.3 mA; V_{CC} = 2.3 V	-	-	0.31	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.44	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.31	V
		I_0 = 4.0 mA; V_{CC} = 3.0 V	-	-	0.44	V
l _l	input leakage current	V_I = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.1	μA
I _{OFF}	power-off leakage current	V_{I} or V_{O} = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.2	μA

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Low-power dual 2-input NAND gate

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
ΔI _{OFF}	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.2	μA
l _{cc}	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.5	μA
∆l _{CC}	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A}; $ [1] $V_{CC} = 3.3 \text{ V}; \text{ per pin}$	-	-	40	μA
CI	input capacitance	V_{CC} = 0 V to 3.6 V; V _I = GND or V _{CC}	-	0.8	-	pF
Co	output capacitance	$V_{O} = GND; V_{CC} = 0 V$	-	1.7	-	pF
T _{amb} = -4	0 °C to +85 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.70 × V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.65 × V _{CC}	-	-	V
Δl _{OFF} ac l _{CC} si Δl _{CC} ac C ₁ in C ₀ oi Tamb -40° V _{IH} H V _{IL} L V _{OH} H V _{OL} L V _{OL} L I ₁ in I _{OFF} p<		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
$ \begin{split} \hline \Delta_{OFF} & \mbox{additional power-off} & \mbox{leakage current} & \mbox{V}_{CC} = 0 \ V to 3.6 \ V; \\ \mbox{V}_{CC} = 0 \ V to 0.2 \ V \\ \mbox{leakage current} & \mbox{V}_{C} = 0 \ V to 3.6 \ V; \\ \mbox{V}_{CC} = 0 \ V to 3.6 \ V; \\ \mbox{Loc} = 0 \ X \ V to 3.6 \ V; \\ \mbox{Loc} = 0 \ X \ V to 3.6 \ V; \\ \mbox{Loc} = 0 \ X \ V to 3.6 \ V; \\ \mbox{Loc} = 0 \ X \ V to 3.6 \ V; \\ \mbox{Loc} = 0 \ X \ V to 3.6 \ V; \\ \mbox{Loc} = 0 \ X \ V to 3.6 \ V; \\ \mbox{Loc} = 0 \ X \ V to 3.6 \ V; \\ \mbox{Loc} = 0 \ X \ V to 3.6 \ V; \\ \mbox{Loc} = 0 \ X \ V \ V \ S \ S \ V; \\ \mbox{Loc} = 0 \ X \ V \ S \ S \ V; \\ \mbox{Loc} = 0 \ X \ V \ S \ S \ V; \\ \mbox{Loc} = 0 \ V \ V \ S \ S \ V; \\ \mbox{Loc} = 0 \ V \ V \ S \ S \ V; \\ \mbox{Loc} = 0 \ V \ V \ S \ S \ V; \\ \mbox{Loc} = 0 \ V \ V \ S \ S \ V; \\ \mbox{Loc} = 0 \ V \ V \ S \ S \ V; \\ \mbox{Loc} = 0 \ V \ V \ S \ S \ V; \\ \mbox{Loc} = 0 \ V \ V \ S \ S \ V; \\ \mbox{Loc} = 0 \ V \ V \ S \ S \ V; \\ \mbox{Loc} = 0 \ V \ V \ S \ S \ V; \\ \mbox{Loc} = 0 \ V \ V \ S \ S \ V; \\ \mbox{Loc} = 0 \ V \ V \ S \ S \ V; \\ \mbox{Loc} = 0 \ V \ V \ S \ S \ S \ V; \\ \mbox{Loc} = 0 \ V \ V \ S \ S \ V; \\ \mbox{Loc} = 0 \ V \ V \ S \ S \ V; \\ \mbox{Loc} = 0 \ V \ S \ S \ S \ V; \\ \mbox{Loc} = 0 \ V \ S \ S \ S \ V; \\ \mbox{Loc} = 0 \ S \ V \ S \ S \ S \ V; \\ \mbox{Loc} = 0 \ S \ V \ S \ S \ S \ S \ S \ S \ S \ S$	-	-	0.30 × V _{CC}	V		
		V _{CC} = 0.9 V to 1.95 V	-	-	0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
C1 i C0 c Tamb = -40 VIH I VIH I VIL I VOH I		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = -20 µA; V_{CC} = 0.8 V to 3.6 V	V _{CC} - 0.1	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.7 × V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	1.03	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.30	-	-	V
		I _O = -2.3 mA; V _{CC} = 2.3 V	1.97	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.85	-	-	V
V _{IH} I V _{IL} I V _{OH} I V _{OL} I I ₁ i		I _O = -2.7 mA; V _{CC} = 3.0 V	2.67	-	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.55	-	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH}$ or V_{IL}				
		I _O = 20 μA; V _{CC} = 0.8 V to 3.6 V	_	-	0.1	V
CO G Tamb = -40 VIH H VIH H VIL L VOH H OFF H AlOFF H ICC S		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	_	-	0.37	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.35	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.33	V
			-	-	0.45	V
			_	-	0.33	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.45	V
l _l	input leakage current	V_{I} = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	_	-	±0.5	μA
	power-off leakage current		-	-	±0.5	μA
	additional power-off	V_{I} or V_{O} = 0 V to 3.6 V;	-	-	±0.6	μA
I _{CC}	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$	-	-	0.9	μA
ΔI _{CC}	additional supply current		-	-	50	μA

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Low-power dual 2-input NAND gate

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = -4	0 °C to +125 °C	· · · · · ·			1	
VIH	HIGH-level input voltage	V _{CC} = 0.8 V	0.75 × V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	$0.70 \times V_{CC}$	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.25 × V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.30 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I_{O} = -20 µA; V_{CC} = 0.8 V to 3.6 V	V _{CC} - 0.11	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	$0.6 \times V_{CC}$	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	0.93	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.17	-	-	V
		I _O = -2.3 mA; V _{CC} = 2.3 V	1.77	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.67	-	-	V
		I _O = -2.7 mA; V _{CC} = 3.0 V	2.40	-	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.30	-	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_0 = 20 µA; V_{CC} = 0.8 V to 3.6 V	-	-	0.11	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.33 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.41	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.39	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.36	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.50	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.36	V
I ₁ inpu I _{OFF} pow		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.50	V
I _I	input leakage current	V_{I} = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.75	μA
I _{OFF}	power-off leakage current			±0.75	μA	
ΔI _{OFF}	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.75	μA
l _{cc}	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μA
ΔI _{CC}	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A};$ [1] $V_{CC} = 3.3 \text{ V}; \text{ per pin}$	-	-	75	μA

[1] One input at V_{CC} - 0.6 V, other input at V_{CC} or GND.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Fig. 5.

Symbol	Parameter	Conditions	T,	_{amb} = 25 °	°C	T _{an} -40 °C te	_{1b} = 0 +85 °C	T _{ar} -40 °C to	_{nb} = o +125 °C	Unit
			Min	Typ[1]	Max	Min	Max	Min	Max	
C _L = 5 p	F									
t _{pd}	propagation	nA, nB to nY; see Fig. 4 [2]								
	delay	V _{CC} = 0.8 V	-	17.5	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	2.5	5.3	11.0	2.1	12.2	2.1	13.5	ns
		V _{CC} = 1.4 V to 1.6 V	2.0	3.8	6.8	1.8	7.8	1.8	8.6	ns
		V _{CC} = 1.65 V to 1.95 V	1.6	3.1	5.3	1.4	6.2	1.4	6.9	ns
		V _{CC} = 2.3 V to 2.7 V	1.3	2.5	4.0	1.1	4.7	1.1	5.2	ns
		V _{CC} = 3.0 V to 3.6 V	1.0	2.2	3.6	1.0	4.2	1.0	4.7	ns
C _L = 10	pF								1	
t _{pd}	propagation	nA, nB to nY; see Fig. 4 [2]								
	delay	V _{CC} = 0.8 V	-	21.0	-	-	-	-	-	ns
	V _{CC} = 1.1 V to 1.3 V	2.4	6.1	13.0	2.2	14.4	2.2	15.9	ns	
		V _{CC} = 1.4 V to 1.6 V	2.4	4.4	7.9	2.2	9.2	2.2	10.2	ns
		V _{CC} = 1.65 V to 1.95 V	2.0	3.7	6.2	1.9	7.3	1.9	8.1	ns
		V _{CC} = 2.3 V to 2.7 V	1.4	3.0	4.7	1.3	5.6	1.3	6.2	ns
		V _{CC} = 3.0 V to 3.6 V	1.3	2.8	4.3	1.2	4.9	1.2	5.4	ns
C _L = 15	pF									
t _{pd}	propagation	nA, nB to nY; see Fig. 4 [2]								
	delay	V _{CC} = 0.8 V	-	24.5	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.4	6.9	14.8	3.1	16.5	3.1	18.2	ns
		V _{CC} = 1.4 V to 1.6 V	2.8	5.0	8.9	2.5	10.5	2.5	11.6	ns
		V _{CC} = 1.65 V to 1.95 V	2.0	4.1	7.0	2.0	8.3	2.0	9.2	ns
		V _{CC} = 2.3 V to 2.7 V	1.7	3.5	5.3	1.5	6.4	1.5	7.1	ns
		V _{CC} = 3.0 V to 3.6 V	1.6	3.2	4.9	1.4	5.7	1.4	6.3	ns
C _L = 30	pF								-	
t _{pd}	propagation	nA, nB to nY; see Fig. 4 [2]								
	delay	V _{CC} = 0.8 V	-	34.8	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	4.6	9.2	20.1	4.1	22.6	4.1	24.9	ns
		V _{CC} = 1.4 V to 1.6 V	3.0	6.5	11.8	2.9	14.0	2.9	15.4	ns
		V _{CC} = 1.65 V to 1.95 V	2.6	5.4	9.3	2.3	11.1	2.3	12.3	ns
		V _{CC} = 2.3 V to 2.7 V	2.4	4.6	7.1	2.1	8.5	2.1	9.4	ns
		V _{CC} = 3.0 V to 3.6 V	2.3	4.3	6.5	2.1	7.6	2.1	8.4	ns

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Symbol	Parameter	Parameter Conditions		T _{amb} = 25 °C		T _{amb} = -40 °C to +85 °C		T _{amb} = -40 °C to +125 °C		Unit	
			Min	Typ[1]	Мах	Min	Max	Min	Max		
C _L = 5 p	F, 10 pF, 15 p	F and 30 pF									
C _{PD}	power dissipation capacitance	$ f_i = 1 \text{ MHz}; $ [3] $ V_I = \text{GND to } V_{\text{CC}} $									
		V _{CC} = 0.8 V	-	2.8	-	-	-	-	-	pF	
		V _{CC} = 1.1 V to 1.3 V	-	2.9	-	-	-	-	-	pF	
		V _{CC} = 1.4 V to 1.6 V	-	3.0	-	-	-	-	-	pF	
		V _{CC} = 1.65 V to 1.95 V	-	3.0	-	-	-	-	-	pF	
		V _{CC} = 2.3 V to 2.7 V	-	3.4	-	-	-	-	-	pF	
		V _{CC} = 3.0 V to 3.6 V	-	3.9	-	-	-	-	-	pF	

All typical values are measured at nominal V_{CC}. [1]

[2]

 t_{Pd} is the same as t_{PLH} and t_{PHL} . C_{PD} is used to determine the dynamic power dissipation (P_D in μ W). [3]

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

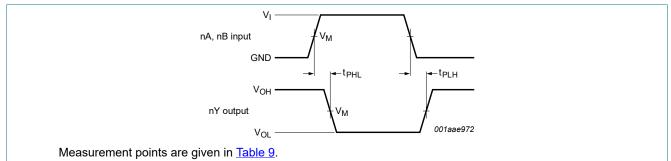
 f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching; $\Sigma(C_L \times V_{CC}^2 \times f_0)$ = sum of outputs.

11.1. Waveform and test circuit



Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig. 4. The data input (nA or nB) to output (nY) propagation delays

Table 9. Measurement points

Supply voltage	Output	Input		
V _{cc}	V _M	V _M	VI	$t_r = t_f$
0.8 V to 3.6 V	0.5 × V _{CC}	0.5 × V _{CC}	V _{CC}	≤ 3.0 ns

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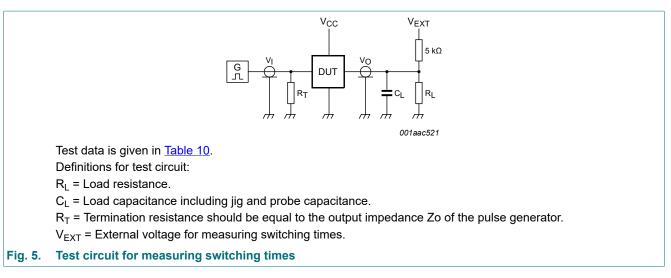


Table 10. Test data

Supply voltage	Load		V _{EXT}		
V _{cc}	CL	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 kΩ or 1 MΩ	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times $R_L = 5 k\Omega$.

For measuring propagation delays, setup and hold times and pulse width R_L = 1 M Ω .

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12. Package outline

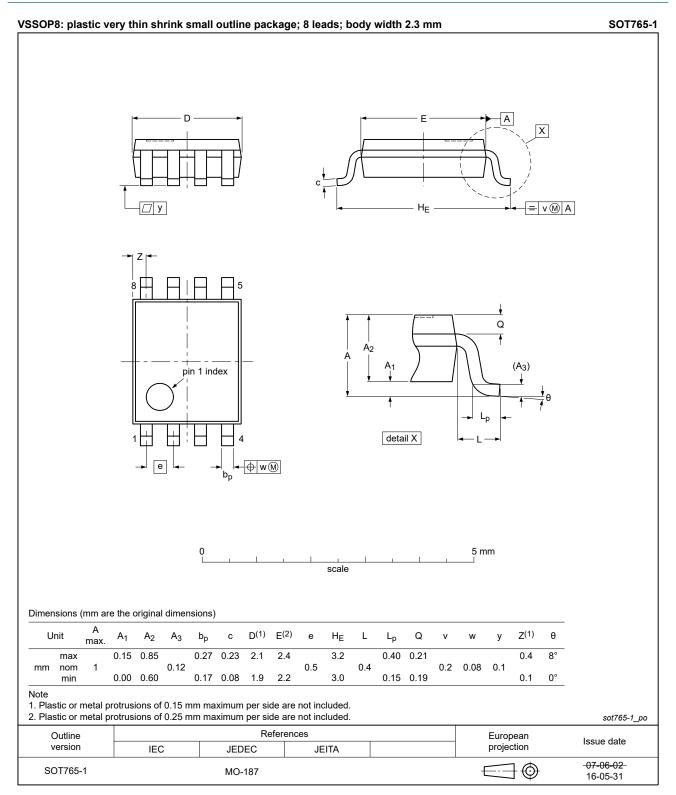


Fig. 6. Package outline SOT765-1 (VSSOP8)

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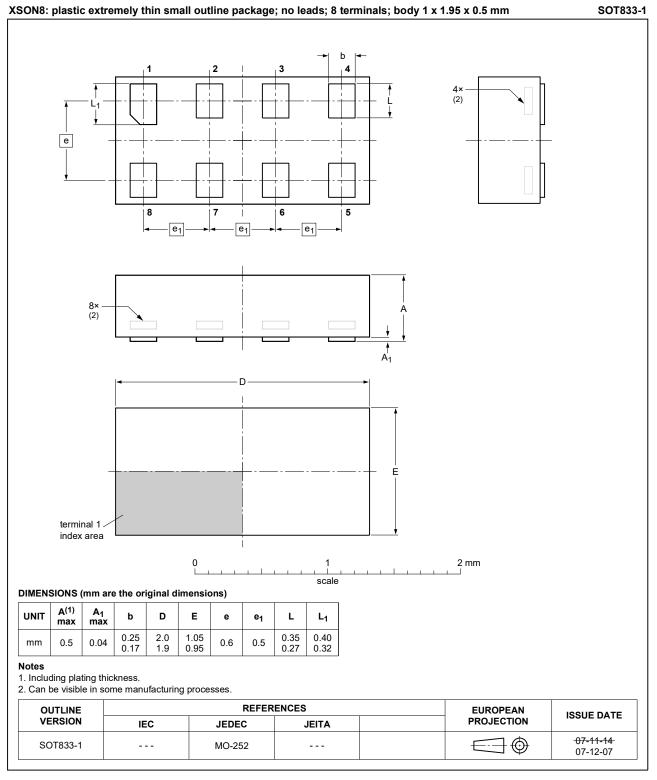
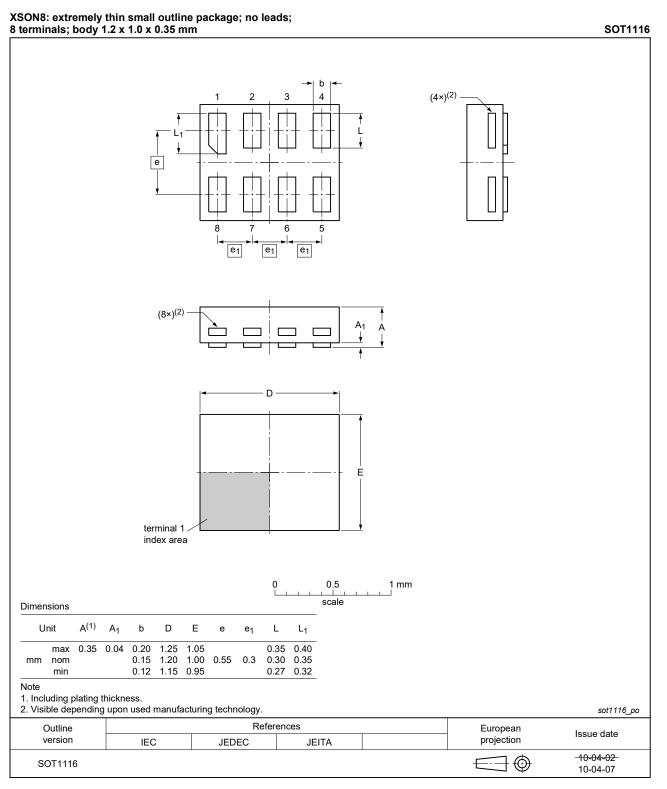


Fig. 7. Package outline SOT833-1 (XSON8)

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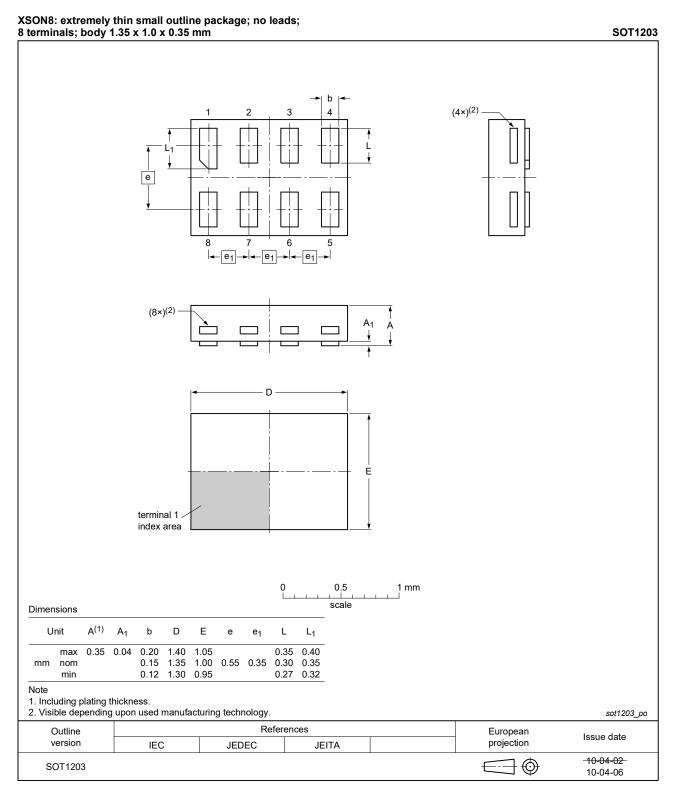
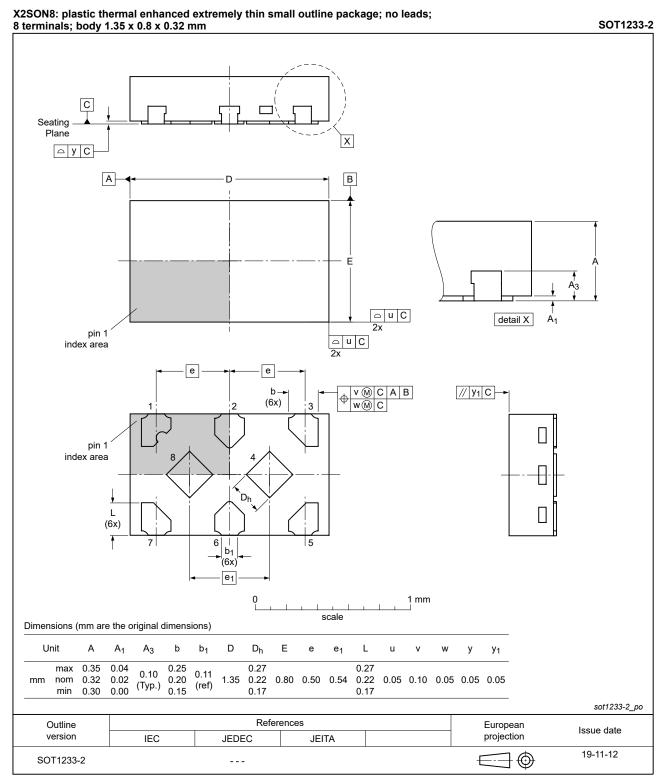


Fig. 9. Package outline SOT1203 (XSON8)

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13. Abbreviations

Table 11. Abbreviations		
Acronym	Description	
ANSI	American National Standards Institute	
CDM	Charged Device Model	
DUT	Device Under Test	
ESD	ElectroStatic Discharge	
ESDA	ElectroStatic Discharge Association	
НВМ	Human Body Model	
JEDEC	Joint Electron Device Engineering Council	

14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
74AUP2G00 v.14	20240812	Product data sheet	-	74AUP2G00 v.13		
Modifications:	Type numbe	Type number 74AUP2G00GM (SOT902-2/XQFN8) removed.				
74AUP2G00 v.13	20240416	Product data sheet	-	74AUP2G00 v.12		
Modifications:	Type numbe	Type number 74AUP2G00GF (SOT1089/XSON8) removed.				
74AUP2G00 v.12	20230714	Product data sheet	-	74AUP2G00 v.11		
Modifications:	• <u>Section 2</u> : E	<u>Section 2</u> : ESD specification updated according to the latest JEDEC standard.				
74AUP2G00 v.11	20220609	Product data sheet	-	74AUP2G00 v.10		
Modifications:						
74AUP2G00 v.10	20170703	Product data sheet	-	74AUP2G00 v.9		
	<u>Section 6.1</u>	nave been adapted to th and <u>Fig. 10</u> (drawings S r 74AUP2G00GD remo	OT1233/X2SON8) ι			
74AUP2G00 v.9	20161028	Product data sheet	-	74AUP2G00 v.8		
Modifications:	Added type	Added type number 74AUP2G00GX (SOT1233/X2SON8)				
74AUP2G00 v.8	20130205	Product data sheet	-	74AUP2G00 v.7		
Modifications:	For type number 74AUP2G00GD XSON8U has changed to XSON8.					
74AUP2G00 v.7	20120608	Product data sheet	-	74AUP2G00 v.6		
74AUP2G00 v.6	20111201	Product data sheet	-	74AUP2G00 v.5		
74AUP2G00 v.5	20101021	Product data sheet	-	74AUP2G00 v.4		
74AUP2G00 v.4	20080605	Product data sheet	-	74AUP2G00 v.3		
74AUP2G00 v.3	20080403	Product data sheet	-	74AUP2G00 v.2		
74AUP2G00 v.2	20070515	Product data sheet	-	74AUP2G00 v.1		
74AUP2G00 v.1	20060825	Product data sheet	-	-		

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at <u>https://www.nexperia.com</u>.

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